

Shania Rehman

List of Publications by Year in descending order

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Version: 2024-02-01

23
papers

503
citations

567281

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677142

22
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23
all docs

23
docs citations

23
times ranked

430
citing authors

#	ARTICLE	IF	CITATIONS
1	Development of directly grown graphene-silicon Schottky barrier solar cell using co-doping technique. International Journal of Energy Research, 2022, 46, 11510-11522.	4.5	11
2	Power efficient transistors with low subthreshold swing using abrupt switching devices. Nano Energy, 2022, 95, 107060.	16.0	16
3	Flexible Diodes with Low Breakdown Voltage for Steep Slope Transistors and One Diode-One Resistor Applications. Advanced Electronic Materials, 2022, 8, .	5.1	8
4	Controlling the Wettability of ZnO Thin Films by Spray Pyrolysis for Photocatalytic Applications. Materials, 2022, 15, 3364.	2.9	16
5	Analog-digital hybrid computing with SnS ₂ memtransistor for low-powered sensor fusion. Nature Communications, 2022, 13, 2804.	12.8	14
6	Tunable resistive switching of vertical ReSe ₂ /graphene hetero-structure enabled by Schottky barrier height and DUV light. Journal of Alloys and Compounds, 2021, 855, 157310.	5.5	37
7	Stable and Multilevel Data Storage Resistive Switching of Organic Bulk Heterojunction. Nanomaterials, 2021, 11, 359.	4.1	28
8	Current Rectification, Resistive Switching, and Stable NDR Effect in BaTiO ₃ /CeO ₂ Heterostructure Devices. Advanced Electronic Materials, 2021, 7, 2001237.	5.1	19
9	Optimization of ZnO:PEIE as an Electron Transport Layer for Flexible Organic Solar Cells. Energy & Fuels, 2021, 35, 12416-12424.	5.1	27
10	Tunable Martensitic Transformation and Magnetic Properties of Sm-Doped NiMnSn Ferromagnetic Shape Memory Alloys. Crystals, 2021, 11, 1115.	2.2	5
11	Discrete memristive levels and logic gate applications of Nb ₂ O ₅ devices. Journal of Alloys and Compounds, 2021, 879, 160385.	5.5	22
12	Effect of oxygen stoichiometry on the threshold switching of RF-sputtered NbO _x (x=2.0-2.5) films. Materials Research Bulletin, 2021, 144, 111492.	5.2	18
13	High mobility ReSe ₂ field effect transistors: Schottky-barrier-height-dependent photoresponsivity and broadband light detection with Co decoration. 2D Materials, 2020, 7, 015010.	4.4	36
14	High performance complementary WS ₂ devices with hybrid Gr/Ni contacts. Nanoscale, 2020, 12, 21280-21290.	5.6	27
15	Neuro-Transistor Based on UV-Treated Charge Trapping in MoTe ₂ for Artificial Synaptic Features. Nanomaterials, 2020, 10, 2326.	4.1	26
16	Multi-heterostructured spin-valve junction of vertical FLG/MoSe ₂ /FLG. APL Materials, 2020, 8, .	5.1	11
17	Chemical Nature of Electrode and the Switching Response of RF-Sputtered NbO _x Films. Nanomaterials, 2020, 10, 2164.	4.1	28
18	Enhanced electrical and broad spectral (UV-Vis-NIR) photodetection in a Gr/ReSe ₂ /Gr heterojunction. Dalton Transactions, 2020, 49, 10017-10027.	3.3	36

#	ARTICLE	IF	CITATIONS
19	Modulation of Magnetoresistance Polarity in BLG/SL-MoSe ₂ Heterostacks. <i>Nanoscale Research Letters</i> , 2020, 15, 136.	5.7	4
20	Thickness-dependent resistive switching in black phosphorus CBRAM. <i>Journal of Materials Chemistry C</i> , 2019, 7, 725-732.	5.5	51
21	Tuning of ionic mobility to improve the resistive switching behavior of Zn-doped CeO ₂ . <i>Scientific Reports</i> , 2019, 9, 19387.	3.3	28
22	Resistive Switching in Solution-Processed Copper Oxide (Cu _x O) by Stoichiometry Tuning. <i>Journal of Physical Chemistry C</i> , 2018, 122, 11076-11085.	3.1	34
23	Optimization of SiO ₂ –TiO ₂ nanocomposite in hole-transporting layer (PEDOT:PSS) for enhanced performance of planar Si-based hybrid solar cells. <i>International Journal of Energy Research</i> , 0, , .	4.5	1